	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	2	6091466.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/31 15:09
2	BRS	L2	2	20010010576.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/31 15:10
3	BRS	L3	2	5760856.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/31 15:34
4	BRS	L4	771	349/38	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/31 16:20

	Type	L #	Hits	Search Text	DBs	Time Stamp
5	BRS	L5	180	4 and semiconductor with (capacit$4 storage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/31 15:36
6	BRS	L6	34	4 and semiconductor with (capacit$4 storage) with (contact adj hole opening)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/31 16:20
7	BRS	L7	101	349/140	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/31 16:34
8	BRS	L8	12	7 and (capacit$4 storage) with (contact adj hole opening)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/31 16:12

	Type	L #	Hits	Search Text	DBs	Time Stamp
9	BRS	L9	3	7 and semiconductor with (capacit$4 storage) with (contact adj hole opening)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/31 16:14
10	BRS	L10	19	7 and semiconductor with (capacit$4 storage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/31 16:14
11	BRS	L11	1463	349/43	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/31 16:20
12	BRS	L12	43	11 and semiconductor with (capacit$4 storage) with (contact adj hole opening)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/31 16:34

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	1585	349/158	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/31 16:34
14	BRS	L14	0	13 and semiconductor with (capacit$4 storage) with (contact adj hole opening)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/31 16:34